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January 2015

FDMS8050ET30

N-Channel PowerTrench® MOSFET
30 V, 423 A, 0.65 mΩ

Features

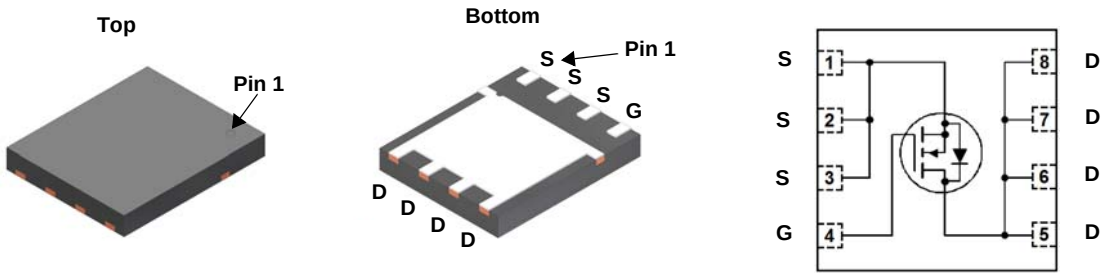
- Extended T_J rating to 175°C
- Max $r_{DS(on)}$ = 0.65 mΩ at V_{GS} = 10 V, I_D = 55 A
- Max $r_{DS(on)}$ = 0.9 mΩ at V_{GS} = 4.5 V, I_D = 47 A
- Advanced Package and Silicon combination for low $r_{DS(on)}$ and high efficiency
- MSL1 robust package design
- 100% UIL tested
- RoHS Compliant

General Description

This N-Channel MOSFET has been designed specifically to improve the overall efficiency and to minimize switch node ringing of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge and extremely low $r_{DS(on)}$.

Applications

- OringFET
- Synchronous Rectifier



Power 56

MOSFET Maximum Ratings T_A = 25 °C unless otherwise noted

Symbol	Parameter			Ratings	Units
V_{DS}	Drain to Source Voltage			30	V
V_{GS}	Gate to Source Voltage		(Note 4)	±20	V
I_D	Drain Current -Continuous	T_C = 25 °C	(Note 6)	423	A
	-Continuous	T_C = 100 °C	(Note 6)	299	
	-Continuous	T_A = 25 °C	(Note 1a)	55	
	-Pulsed		(Note 5)	1914	
E_{AS}	Single Pulse Avalanche Energy		(Note 3)	1536	mJ
P_D	Power Dissipation	T_C = 25 °C		180	W
	Power Dissipation	T_A = 25 °C	(Note 1a)	3.3	
T_J, T_{STG}	Operating and Storage Junction Temperature Range			-55 to +175	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.83	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	45	

Package Marking and Ordering Information

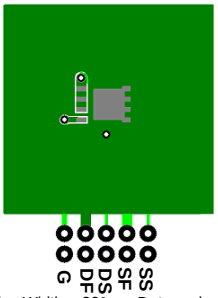
Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMS8050ET	FDMS8050ET30	Power 56	13 ”	12 mm	3000 units

Electrical Characteristics T_J = 25 °C unless otherwise noted

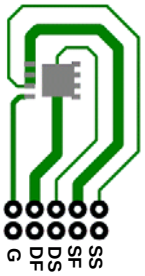
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 750 μA, V_{GS} = 0 V	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 750 μA, referenced to 25 °C		20		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 24 V, V_{GS} = 0 V			1	μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = 20 V, V_{DS} = 0 V			100	nA
On Characteristics						
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 750 μA	1.0	1.8	3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 750 μA, referenced to 25 °C		-6		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 55 A		0.5	0.65	mΩ
		V_{GS} = 4.5 V, I_D = 47 A		0.7	0.9	
		V_{GS} = 10 V, I_D = 55 A, T_J = 125 °C		0.7	0.9	
g_{FS}	Forward Transconductance	V_{DS} = 5 V, I_D = 55 A		333		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHz		16150	22610	pF
C_{oss}	Output Capacitance			4455	6240	pF
C_{rss}	Reverse Transfer Capacitance			220	310	pF
R_g	Gate Resistance			1.0	3.0	Ω
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 15 V, I_D = 55 A, V_{GS} = 10 V, R_{GEN} = 6 Ω		29	47	ns
t_r	Rise Time			22	36	ns
$t_{d(off)}$	Turn-Off Delay Time			87	139	ns
t_f	Fall Time			16	28	ns
Q_g	Total Gate Charge	V_{GS} = 0 V to 10 V; V_{DD} = 15 V, I_D = 55 A		204	285	nC
Q_g	Total Gate Charge	V_{GS} = 0 V to 4.5 V; V_{DD} = 15 V, I_D = 55 A		93	130	nC
Q_{gs}	Gate to Source Charge	V_{DD} = 15 V, I_D = 55 A		41		nC
Q_{gd}	Gate to Drain “Miller” Charge	V_{DD} = 15 V, I_D = 55 A		18		nC
Drain-Source Diode Characteristics						
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = 2.2 A (Note 2)		0.64	1.2	V
		V_{GS} = 0 V, I_S = 55 A (Note 2)		0.74	1.2	
t_{rr}	Reverse Recovery Time	I_F = 55 A, di/dt = 100 A/μs		77	124	ns
Q_{rr}	Reverse Recovery Charge			141	226	nC

Notes:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in^2 pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta CA}$ is determined by the user's board design.



a. 45 °C/W when mounted on a 1 in^2 pad of 2 oz copper.



b. 115 °C/W when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.

3. E_{AS} of 1536 mJ is based on starting T_J = 25 °C, L = 3 mH, I_{AS} = 32 A, V_{DD} = 30 V, V_{GS} = 10 V, 100% test at L = 0.3 mH, I_{AS} = 69 A.

4. As an N-ch device, the negative Vgs rating is for low duty cycle pulse occurrence only. No continuous rating is implied

5. Pulse Id please refer to Fig.11 SOA curve for detail.

6. Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro-mechanical application board design.

Typical Characteristics T_J = 25 °C unless otherwise noted

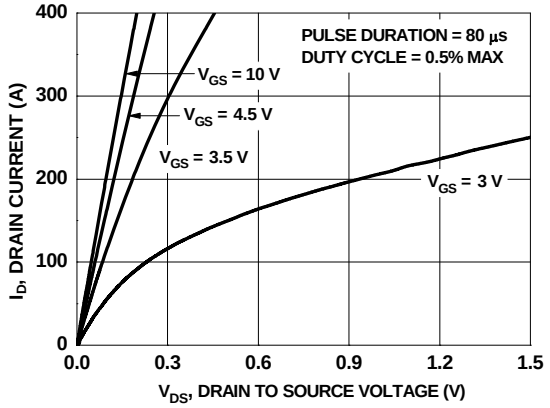


Figure 1. On-Region Characteristics

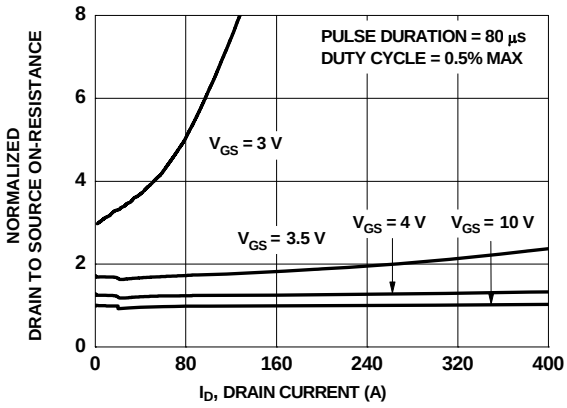


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

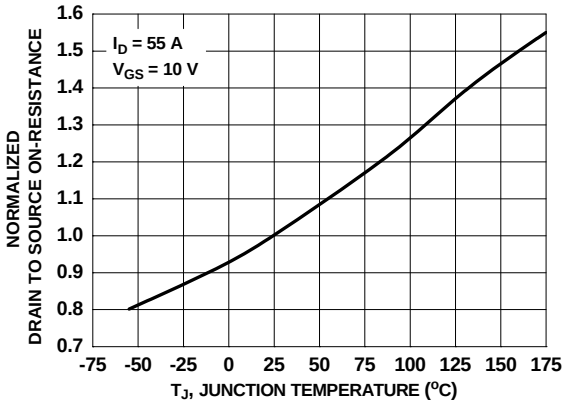


Figure 3. Normalized On-Resistance vs Junction Temperature

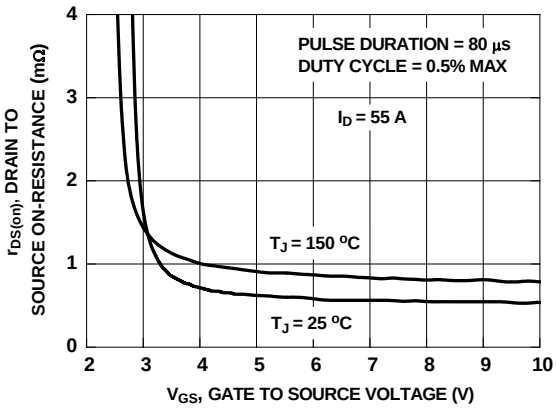


Figure 4. On-Resistance vs Gate to Source Voltage

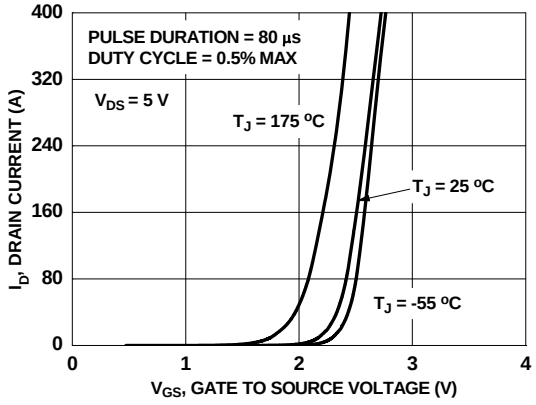


Figure 5. Transfer Characteristics

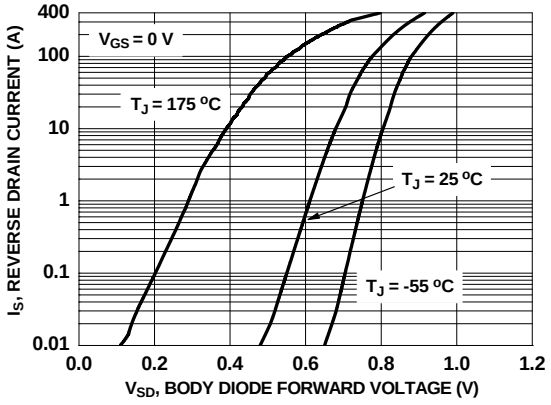


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25 °C unless otherwise noted

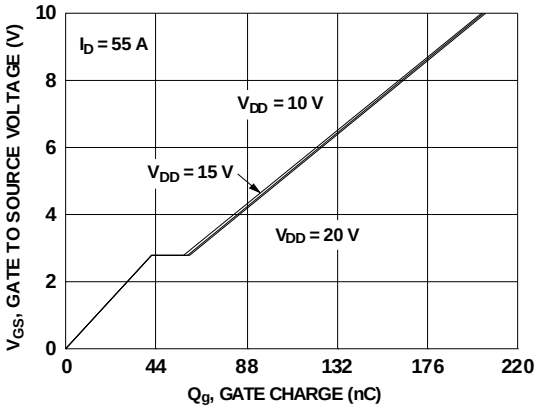


Figure 7. Gate Charge Characteristics

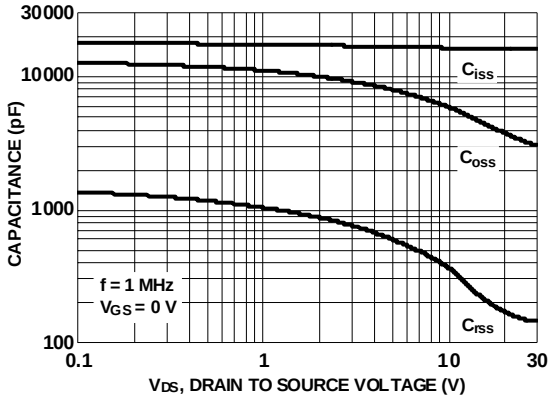


Figure 8. Capacitance vs Drain to Source Voltage

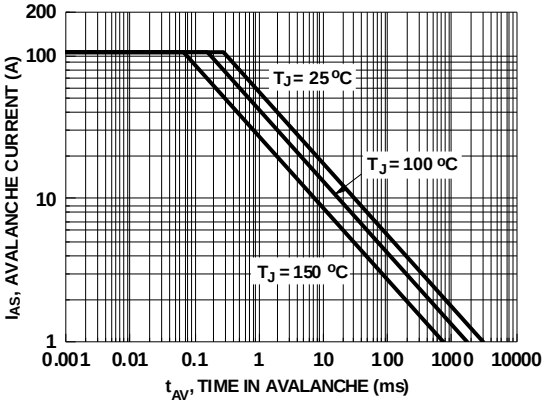


Figure 9. Unclamped Inductive Switching Capability

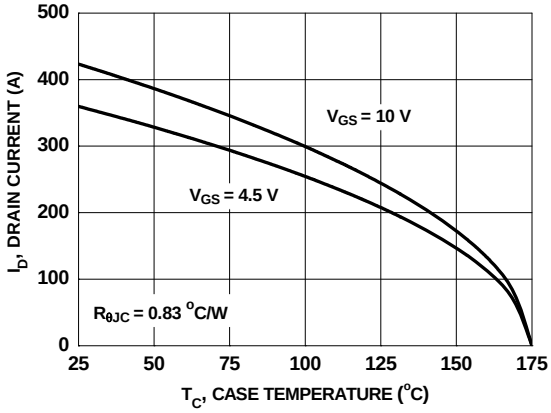


Figure 10. Maximum Continuous Drain Current vs Case Temperature

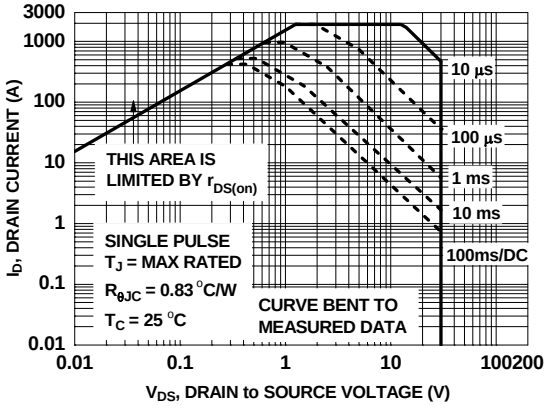


Figure 11. Forward Bias Safe Operating Area

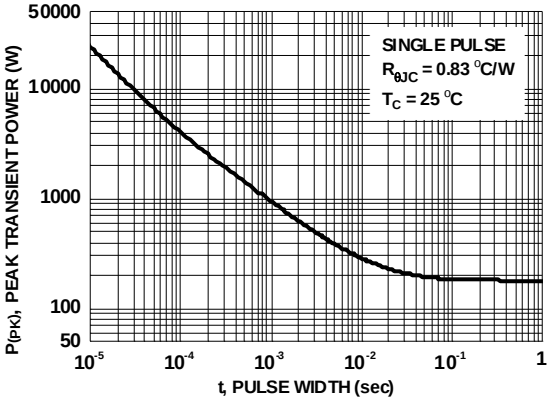


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics T_J = 25 °C unless otherwise noted

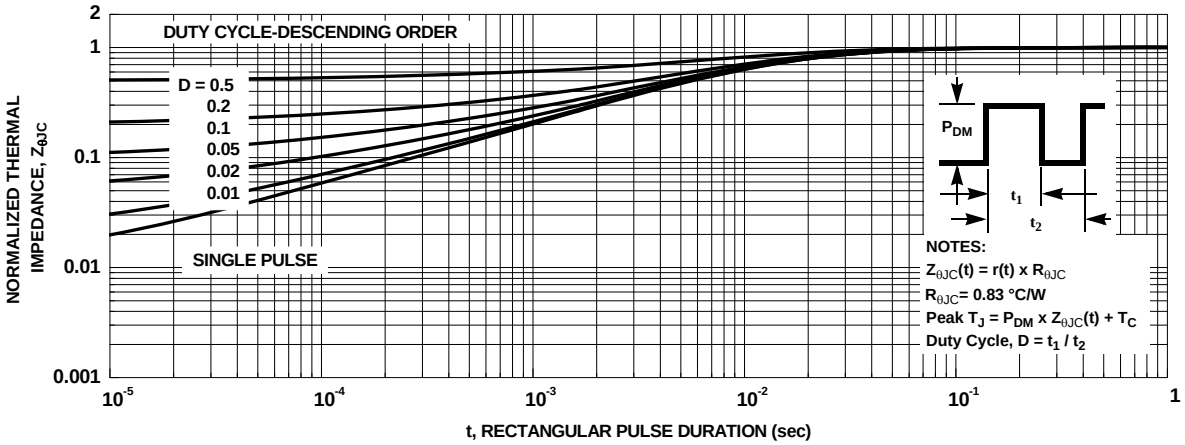
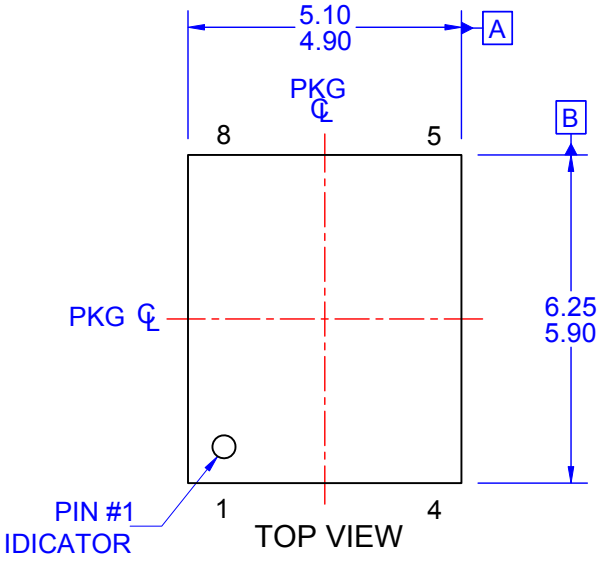
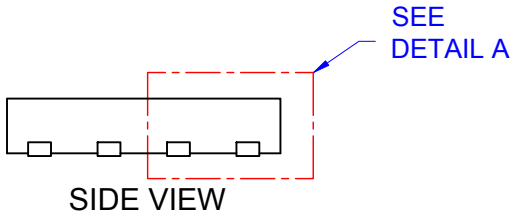
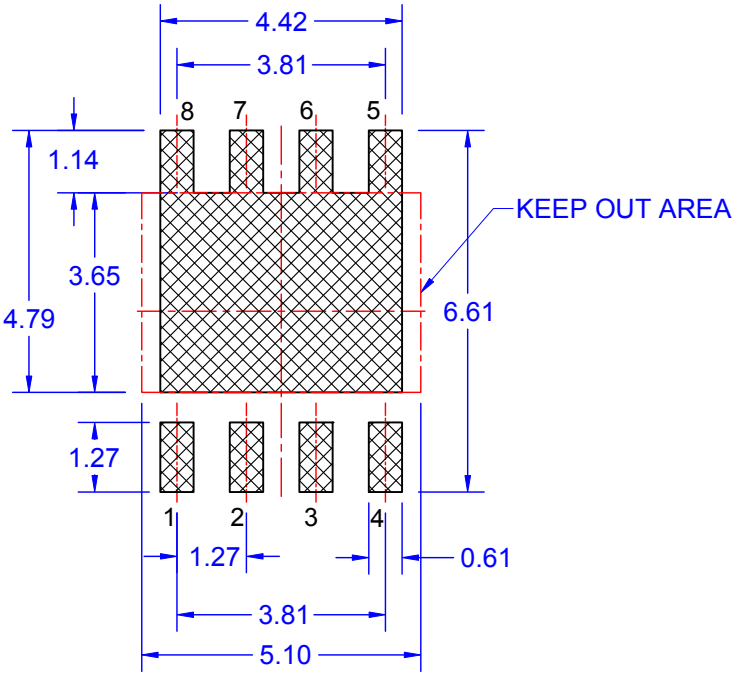
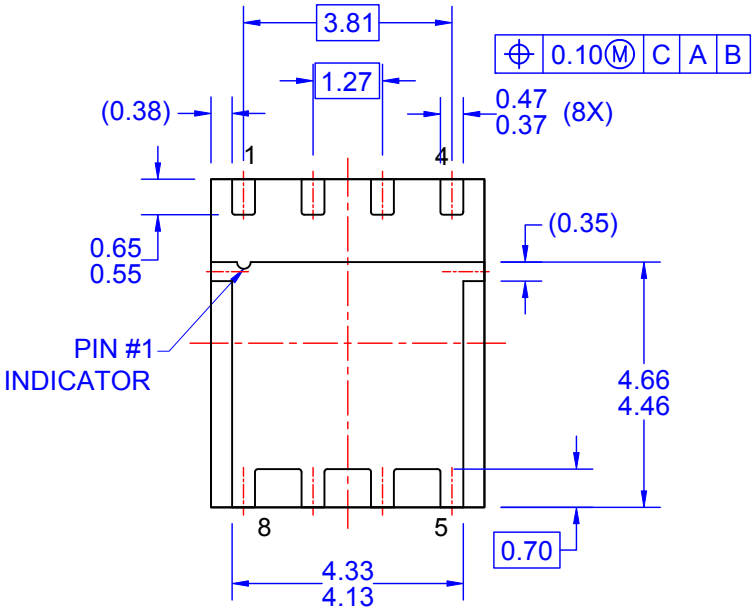


Figure 13. Junction-to-Ambient Transient Thermal Response Curve









NOTES: UNLESS OTHERWISE SPECIFIED

A) PACKAGE STANDARD REFERENCE: JEDEC MO-240, ISSUE A, VAR. AA,

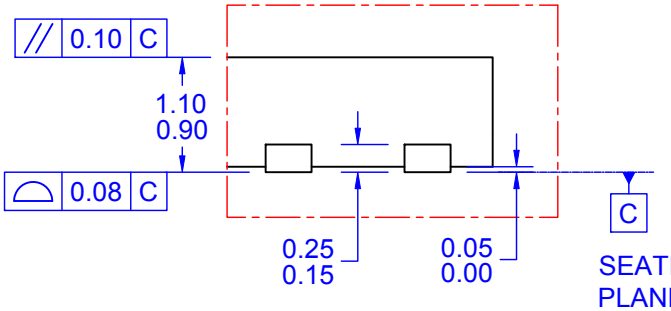
B) ALL DIMENSIONS ARE IN MILLIMETERS.

C) DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.

D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.

E) IT IS RECOMMENDED TO HAVE NO TRACES OR VIAS WITHIN THE KEEP OUT AREA.

F) DRAWING FILE NAME: PQFN08JREV3.



DETAIL A

SCALE: 2:1

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